

16. (New) The ceramic substrate according to claim 7,

wherein said conductor layer is any of a chuck top electrode, a guard electrode and a ground electrode.

IN THE ABSTRACT OF THE DISCLOSURE

Please amend the Abstract on page 45 as follows:

ABSTRACT

A ceramic substrate in which even if rapid temperature rising or rapid temperature falling is conducted, no problem of cracking or warp of the ceramic substrate occurs. In a case that the ceramic substrate is a ceramic substrate constituting an electrostatic chuck, local dispersion of chuck power is eliminated, in a case that the ceramic substrate is a ceramic substrate constituting a hot plate, local dispersion of temperature of a wafer treating face is eliminated, and in a case that the ceramic substrate is a ceramic substrate constituting a wafer prober, dispersion of applied voltage of a guard electrode or a ground electrode is eliminated and a stray capacitor or noise can be eliminated. The ceramic substrate is a ceramic substrate provided with a conductor layer on the surface of the ceramic substrate or inside the ceramic substrate, in which the ratio ( $t_2/t_1$ ) of the average thickness of the conductor layer ( $t_2$ ) to the average thickness of the ceramic substrate ( $t_1$ ) is less than 0.1, and a dispersion of the thickness of the conductor layer to the average thickness of the conductor layer is in a range of -70 to +150%.